

# 74AUP1G74

Low-power D-type flip-flop with set and reset; positive-edge trigger

Rev. 04 — 3 June 2008

Product data sheet

## 1. General description

The 74AUP1G74 provides a low-power, low-voltage single positive-edge triggered D-type flip-flop with individual data (D), clock (CP), set ( $\overline{SD}$ ) and reset ( $\overline{RD}$ ) inputs and complementary Q and  $\overline{Q}$  outputs. The  $\overline{SD}$  and  $\overline{RD}$  are asynchronous active LOW inputs and operate independently of the clock input. Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

## 2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114E Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101C exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40 \text{ }^\circ\text{C}$  to  $+85 \text{ }^\circ\text{C}$  and  $-40 \text{ }^\circ\text{C}$  to  $+125 \text{ }^\circ\text{C}$

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1G74DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP1G74GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74AUP1G74GD	-40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
74AUP1G74GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

### 4. Marking

Table 2. Marking codes

Type number	Marking code
74AUP1G74DC	p74
74AUP1G74GT	p74
74AUP1G74GD	p74
74AUP1G74GM	p74

### 5. Functional diagram

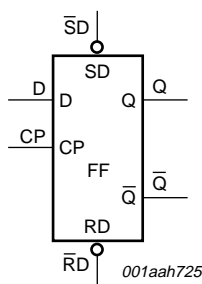


Fig 1. Logic symbol

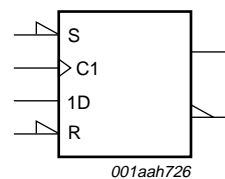
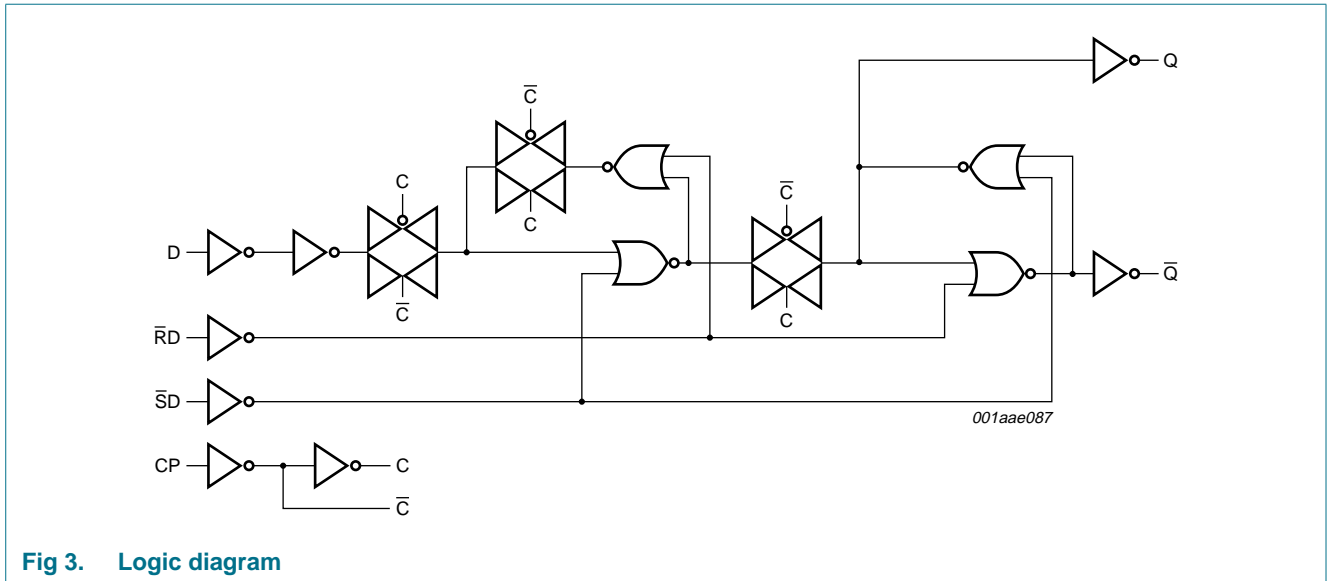
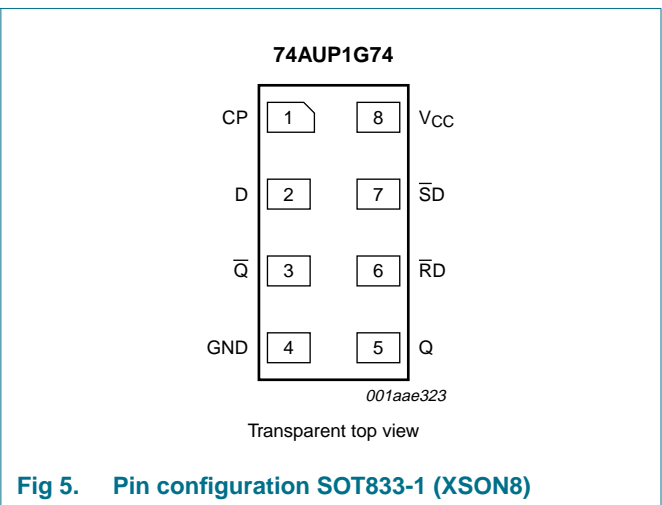
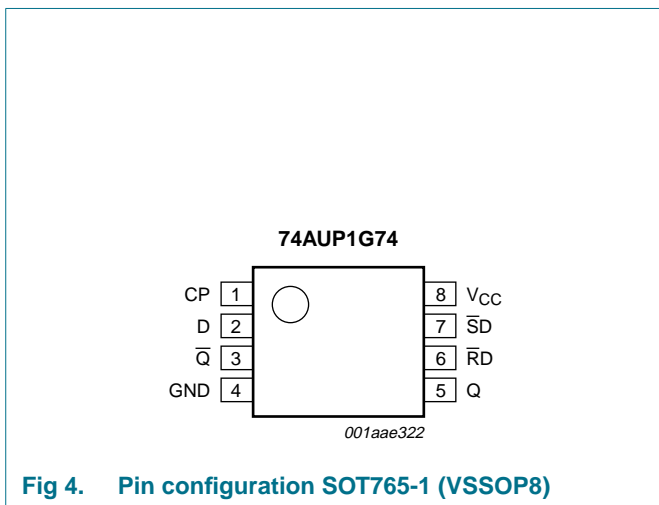


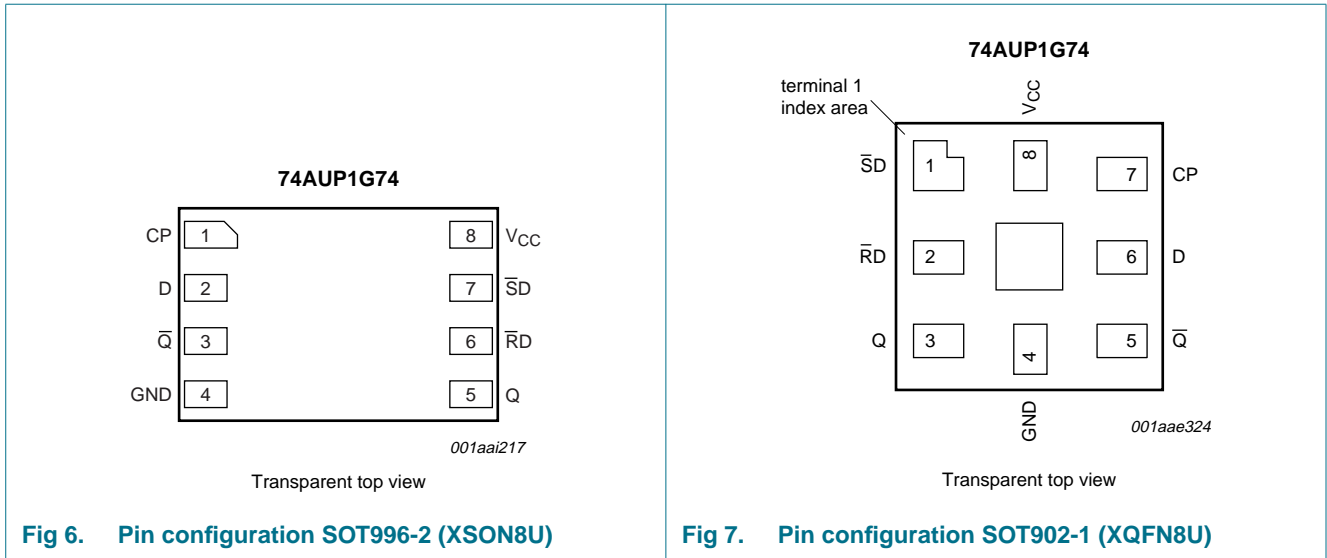
Fig 2. IEC logic symbol



## 6. Pinning information

### 6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
CP	1	7	clock input
D	2	6	data input
$\bar{Q}$	3	5	complement output
GND	4	4	ground (0 V)
Q	5	3	true output
$\bar{RD}$	6	2	asynchronous reset input (active LOW)
$\bar{SD}$	7	1	asynchronous set input (active LOW)
V <sub>CC</sub>	8	8	supply voltage

7. Functional description

Table 4. Function table for asynchronous operation<sup>[1]</sup>

Input				Output	
$\bar{SD}$	$\bar{RD}$	CP	D	Q	$\bar{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H	H

[1] H = HIGH voltage level;  
 L = LOW voltage level;  
 X = don't care.

**Table 5. Function table for synchronous operation<sup>[1]</sup>**

Input				Output	
SD	RD	CP	D	Q <sub>n+1</sub>	$\bar{Q}_{n+1}$
H	H	↑	L	L	H
H	H	↑	H	H	L

- [1] H = HIGH voltage level;
- L = LOW voltage level;
- X = don't care;
- ↑ = LOW-to-HIGH CP transition;
- Q<sub>n+1</sub> = state after the next LOW-to-HIGH CP transition.

## 8. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
V <sub>I</sub>	input voltage		[1] -0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
V <sub>O</sub>	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
I <sub>O</sub>	output current	V <sub>O</sub> = 0 V to V <sub>CC</sub>	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2] -	250	mW

- [1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- [2] For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly with 8.0 mW/K.  
For XSON8, XSON8U and XQFN8U packages: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 7. Operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
V <sub>I</sub>	input voltage		0	3.6	V
V <sub>O</sub>	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 0.8 V to 3.6 V	-	200	ns/V

## 10. Static characteristics

**Table 8. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V; per pin	<a href="#">[1]</a>	-	40	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.6	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.3	-	pF

**Table 8. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.6	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V; per pin	[1]	-	50	μA

**Table 8. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.75 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.25 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.6 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.75	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.75	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V; per pin	[1]	-	75	μA

[1] One input at V<sub>CC</sub> - 0.6 V, other input at V<sub>CC</sub> or GND.



## 11. Dynamic characteristics

**Table 9. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q, $\bar{Q}$ ; see <a href="#">Figure 8</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	25.4	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.9	6.7	14.0	2.6	14.2	2.6	14.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.4	4.5	7.6	2.3	8.3	2.3	8.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.9	3.5	5.7	1.7	6.5	1.7	6.8	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	2.6	3.8	1.4	4.4	1.4	4.7	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.5	2.2	3.1	1.2	3.4	1.2	3.7	ns
		$\bar{S}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	19.6	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.7	5.6	11.0	2.5	11.4	2.5	11.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.4	4.0	6.3	2.2	6.9	2.2	7.3	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.0	3.3	4.9	1.7	5.6	1.7	5.9	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.9	2.7	3.7	1.7	4.0	1.7	4.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.8	2.5	3.2	1.5	3.6	1.5	3.8	ns
		$\bar{R}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	19.2	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.6	5.5	11.0	2.5	11.3	2.5	11.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.3	3.9	6.3	2.2	6.8	2.2	7.3	ns
V <sub>CC</sub> = 1.65 V to 1.95 V	1.9	3.2	5.0	1.8	5.6	1.8	5.9	ns		
V <sub>CC</sub> = 2.3 V to 2.7 V	1.9	2.6	3.6	1.7	4.1	1.7	4.3	ns		
V <sub>CC</sub> = 3.0 V to 3.6 V	1.8	2.4	3.3	1.5	3.6	1.5	3.8	ns		
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 0.8 V	-	53	-	-	-	-	MHz	
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	203	-	170	-	170	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	347	-	310	-	300	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	435	-	400	-	390	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	550	-	490	-	480	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	619	-	550	-	510	-	MHz

**Table 9. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
<b>C<sub>L</sub> = 10 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q, $\bar{Q}$ ; see <a href="#">Figure 8</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	28.9	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.1	7.5	15.8	2.9	16.1	2.9	16.1	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.7	5.1	8.7	2.4	9.4	2.4	9.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.5	4.1	6.5	2.2	7.2	2.2	7.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.0	3.2	4.6	1.8	5.3	1.8	5.6	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.8	2.8	3.8	1.6	4.1	1.6	4.4	ns
		$\bar{S}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	23.2	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.9	6.5	12.9	2.8	13.3	2.8	13.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.7	4.6	7.5	2.3	7.9	2.3	8.3	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.6	3.9	5.6	2.3	6.3	2.3	6.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.3	3.2	4.4	2.0	4.8	2.0	5.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.2	3.0	3.9	1.9	4.2	1.9	4.4	ns
		$\bar{R}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	22.7	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.8	6.4	12.8	2.7	13.2	2.7	13.4	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.6	4.5	7.5	2.3	8.1	2.3	8.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.5	3.3	5.8	2.3	6.3	2.3	6.7	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.2	3.2	4.4	2.0	4.9	2.0	5.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	2.9	4.0	1.9	4.3	1.9	4.5	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 0.8 V	-	52	-	-	-	-	MHz	
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	192	-	150	-	150	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	324	-	280	-	230	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	421	-	310	-	250	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	486	-	370	-	360	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	550	-	410	-	360	-	MHz

**Table 9. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
<b>C<sub>L</sub> = 15 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q, $\bar{Q}$ ; see <a href="#">Figure 8</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	32.4	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.5	8.3	17.6	3.3	17.8	3.3	18.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.2	5.6	9.5	2.8	10.5	2.8	11.1	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.7	4.6	7.2	2.5	8.1	2.5	8.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.4	3.6	5.2	2.2	5.8	2.2	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.2	3.2	4.4	2.0	4.9	2.0	5.2	ns
		$\bar{S}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	26.7	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.3	7.3	14.7	3.1	15.2	3.1	15.4	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.2	5.2	8.3	2.9	9.0	2.9	9.5	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.8	4.3	6.4	2.5	7.1	2.5	7.5	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.8	3.7	5.1	2.2	5.5	2.2	5.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.5	3.5	4.6	2.4	5.0	2.4	5.2	ns
		$\bar{R}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	26.1	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.2	7.2	14.5	3.1	15.0	3.1	15.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.1	5.1	8.4	2.7	9.2	2.7	9.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.7	4.3	6.5	2.6	7.3	2.6	7.7	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.6	3.6	5.0	2.4	5.5	2.4	5.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.4	3.4	4.6	2.3	5.0	2.3	5.2	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 0.8 V	-	50	-	-	-	-	MHz	
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	181	-	120	-	120	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	301	-	190	-	160	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	407	-	240	-	190	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	422	-	300	-	270	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	481	-	320	-	300	-	MHz

**Table 9. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
<b>C<sub>L</sub> = 30 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q, $\bar{Q}$ ; see <a href="#">Figure 8</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	42.7	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.2	10.6	22.5	4.0	23.0	4.0	23.3	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.7	7.2	12.0	3.7	13.3	3.7	14.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.5	5.8	9.2	3.4	10.4	3.4	11.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.3	4.7	6.6	3.0	7.3	3.0	7.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.0	4.3	5.8	2.8	6.8	2.8	7.3	ns
		$\bar{S}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	37.0	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.0	9.5	19.8	3.8	20.8	3.8	21.1	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.8	6.7	10.9	3.7	12.0	3.7	12.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.7	5.6	8.4	3.5	9.3	3.5	9.9	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.7	4.8	6.6	3.2	7.2	3.2	7.6	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.4	4.6	6.0	3.1	6.8	3.1	7.1	ns
		$\bar{R}D$ to Q, $\bar{Q}$ ; see <a href="#">Figure 9</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	36.4	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.9	9.4	19.5	3.8	20.2	3.8	20.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.6	6.6	10.9	3.7	12.0	3.7	12.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.5	5.5	8.5	3.5	9.5	3.5	10.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.5	4.7	6.5	3.2	7.1	3.2	7.6	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.3	4.4	6.1	3.1	7.1	3.1	7.5	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 0.8 V	-	28	-	-	-	-	MHz	
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	145	-	70	-	70	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	185	-	120	-	110	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	270	-	150	-	120	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	290	-	190	-	170	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	315	-	200	-	190	-	MHz

**Table 9. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF, 10 pF, 15 pF and 30 pF</b>										
t <sub>su</sub>	set-up time	D to CP HIGH; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	3.4	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	0.6	-	1.2	-	1.2	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	0.3	-	0.6	-	0.6	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.4	-	0.5	-	0.5	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.2	-	0.4	-	0.4	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.3	-	0.4	-	0.4	-	ns
		D to CP LOW; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	3.0	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	0.5	-	1.2	-	1.2	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	0.3	-	0.7	-	0.7	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.4	-	0.7	-	0.7	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.5	-	0.7	-	0.7	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.6	-	0.8	-	0.8	-	ns
t <sub>h</sub>	hold time	D to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	-1.9	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	-0.3	-	0.5	-	0.5	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	-0.2	-	0.2	-	0.2	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	-0.2	-	0.1	-	0.1	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-0.2	-	0.1	-	0.1	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-0.2	-	0.1	-	0.1	-	ns
t <sub>rec</sub>	recovery time	$\overline{RD}$ ; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	-0.5	-	-0.9	-	-0.9	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	-0.2	-	-0.6	-	-0.6	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	-0.2	-	-0.4	-	-0.4	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-0.1	-	-0.1	-	-0.1	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-0.1	-	-0.1	-	-0.1	-	ns
		$\overline{SD}$ ; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	-0.5	-	-0.3	-	-0.3	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	-0.4	-	-0.1	-	-0.1	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	-0.3	-	0	-	0	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-0.2	-	0.1	-	0.1	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-0.1	-	0.1	-	0.1	-	ns

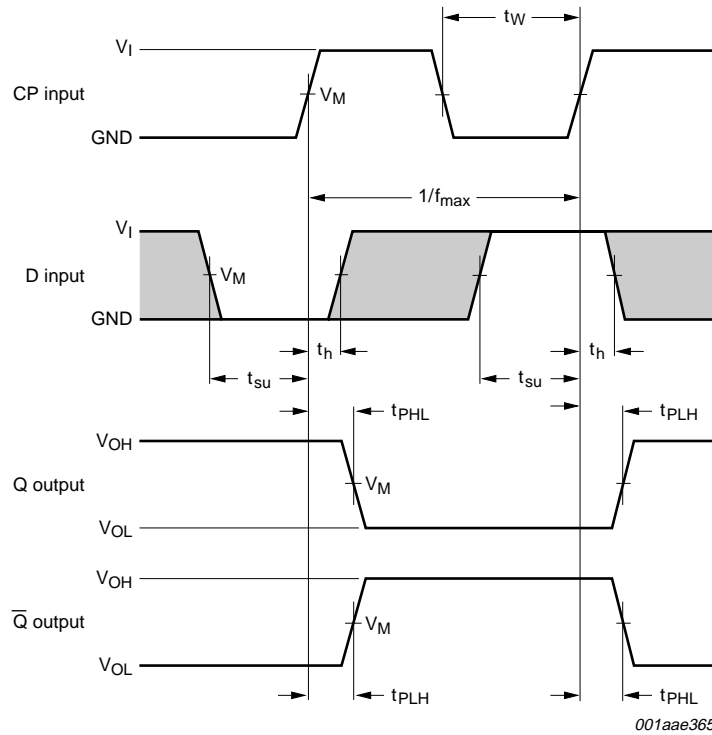
**Table 9. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
t <sub>w</sub>	pulse width	CP HIGH or LOW; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.1	-	2.7	-	2.7	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	1.1	-	1.5	-	1.5	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.9	-	1.6	-	1.6	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.6	-	1.7	-	1.7	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.6	-	1.9	-	1.9	-	ns
		SD or RD LOW; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	4.2	-	11.3	-	11.5	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	2.3	-	6.2	-	6.4	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	1.8	-	4.8	-	5.0	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	1.2	-	3.3	-	3.5	-	ns
V <sub>CC</sub> = 3.0 V to 3.6 V	-	1.1	-	2.6	-	2.8	-	ns		
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; <sup>[3]</sup> V <sub>I</sub> = GND to V <sub>CC</sub>								
		V <sub>CC</sub> = 0.8 V	-	2.8	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.9	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	3.0	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.0	-	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.5	-	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	3.9	-	-	-	-	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of outputs.

12. Waveforms



Measurement points are given in [Table 10](#).

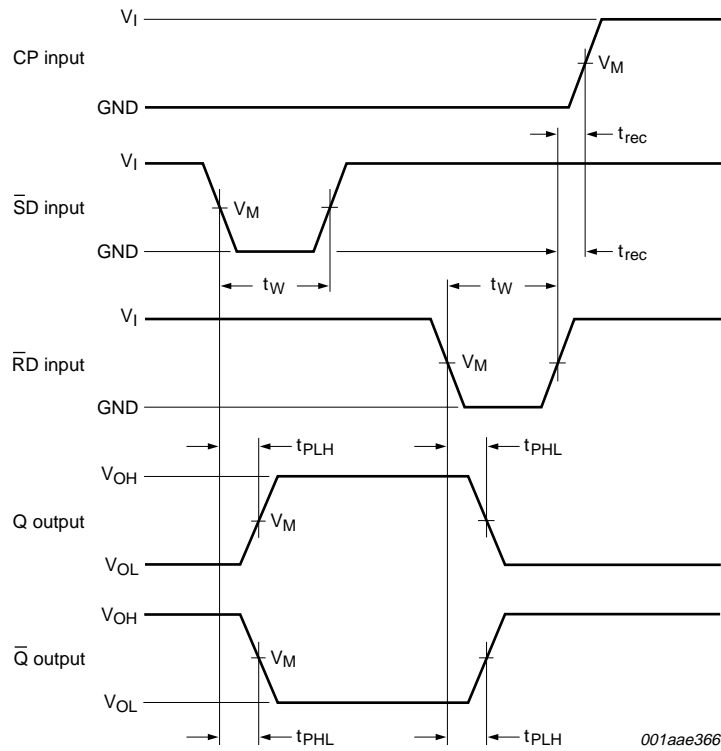
The shaded areas indicate when the input is permitted to change for predictable output performance.

$V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 8.** The clock input (CP) to output (Q, Q̄) propagation delays, the data input (D) to clock input (CP) set-up and hold times and the clock input (CP) pulse width and maximum frequency

**Table 10.** Measurement points

Supply voltage	Output	Input		
$V_{CC}$	$V_M$	$V_M$	$V_I$	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{CC}$	$\leq 3.0$ ns

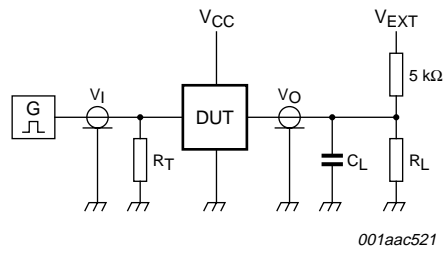


Measurement points are given in [Table 10](#).

$V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 9.** The set input ( $\overline{SD}$ ) and reset input ( $\overline{RD}$ ) to output (Q,  $\overline{Q}$ ) propagation delays, the set input ( $\overline{SD}$ ) and reset input ( $\overline{RD}$ ) pulse widths and the reset input ( $\overline{RD}$ ) to clock input (CP) recovery time





Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 10. Load circuitry for switching times**

**Table 11. Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$

For measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

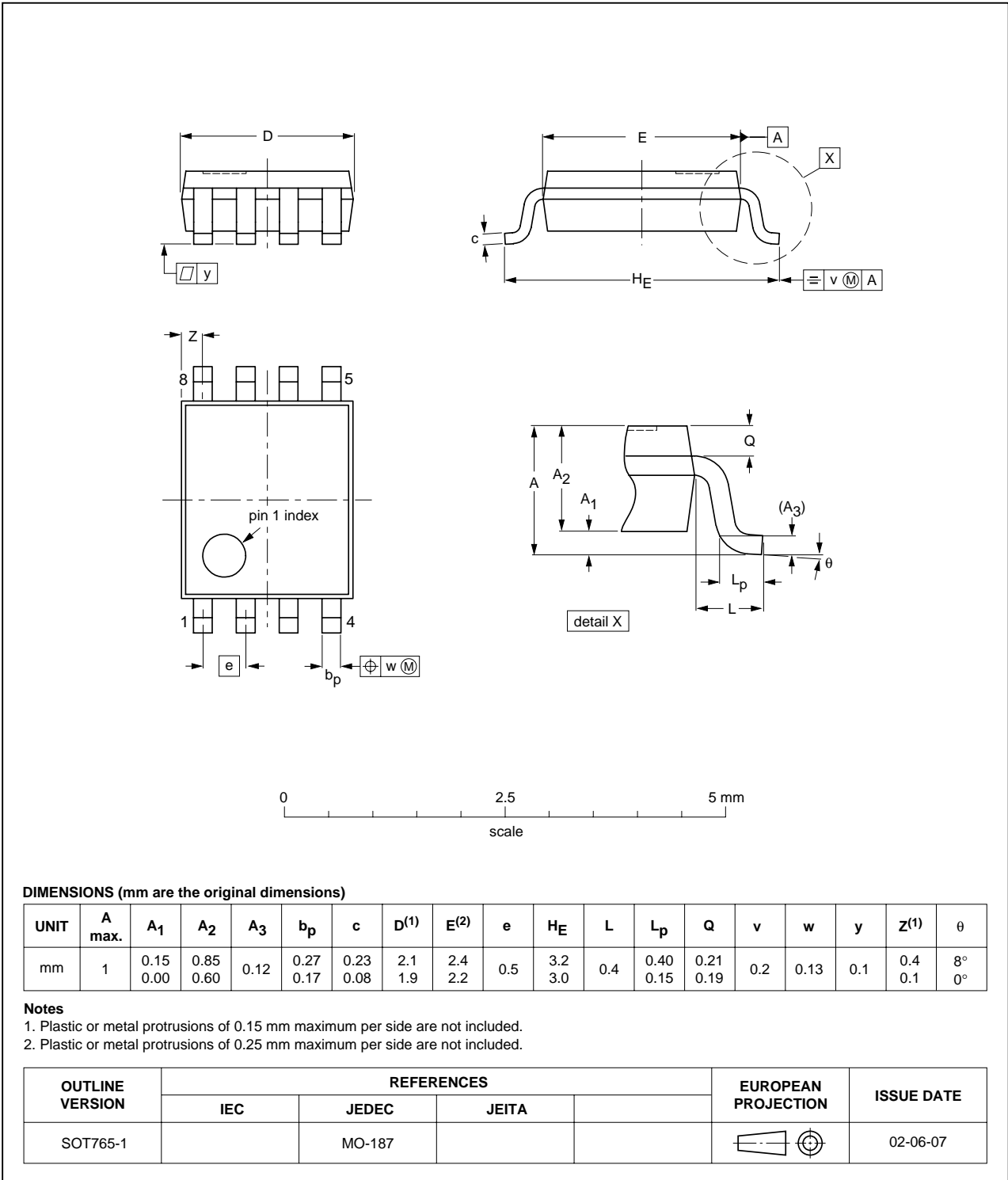


Fig 11. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

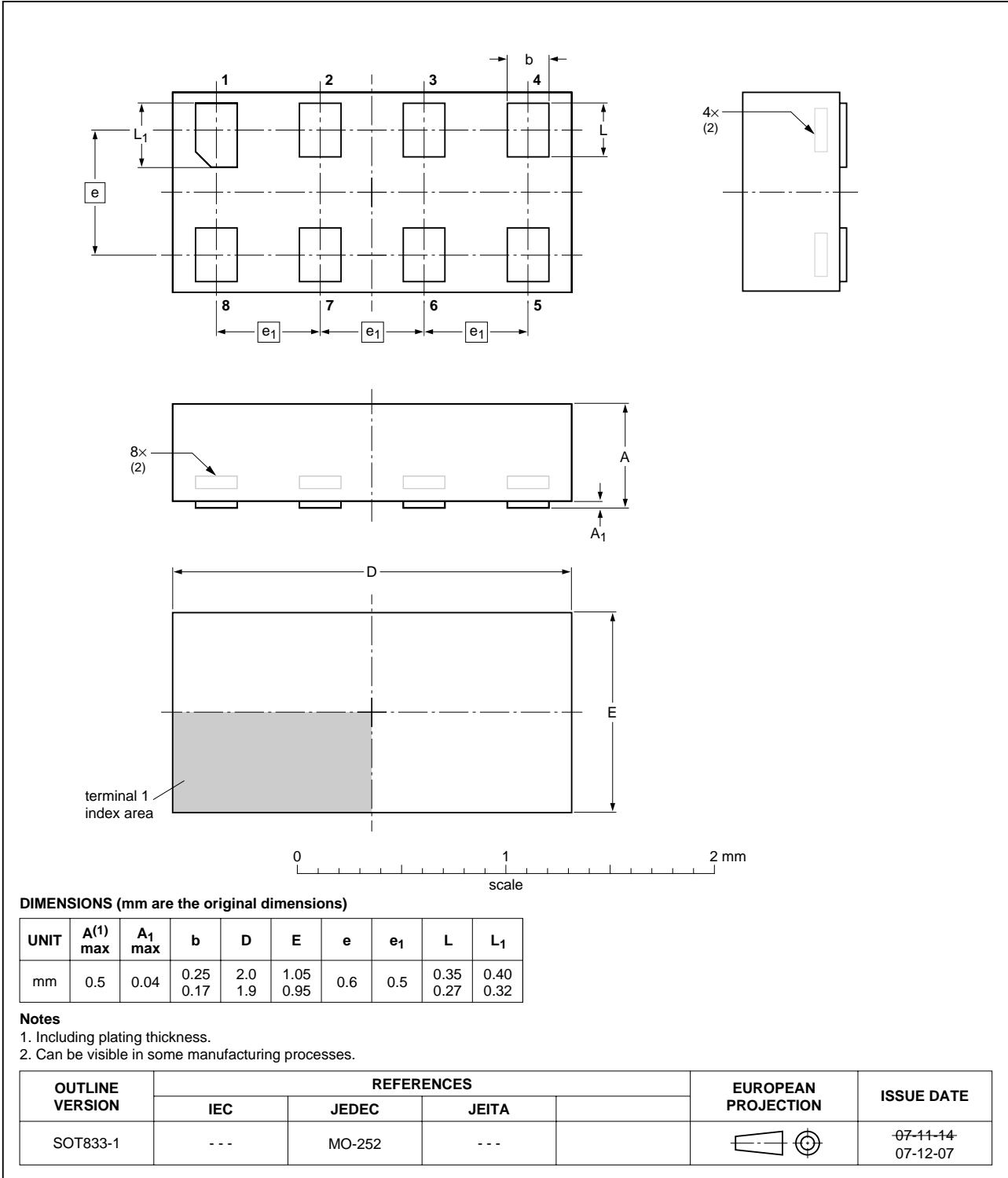


Fig 12. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

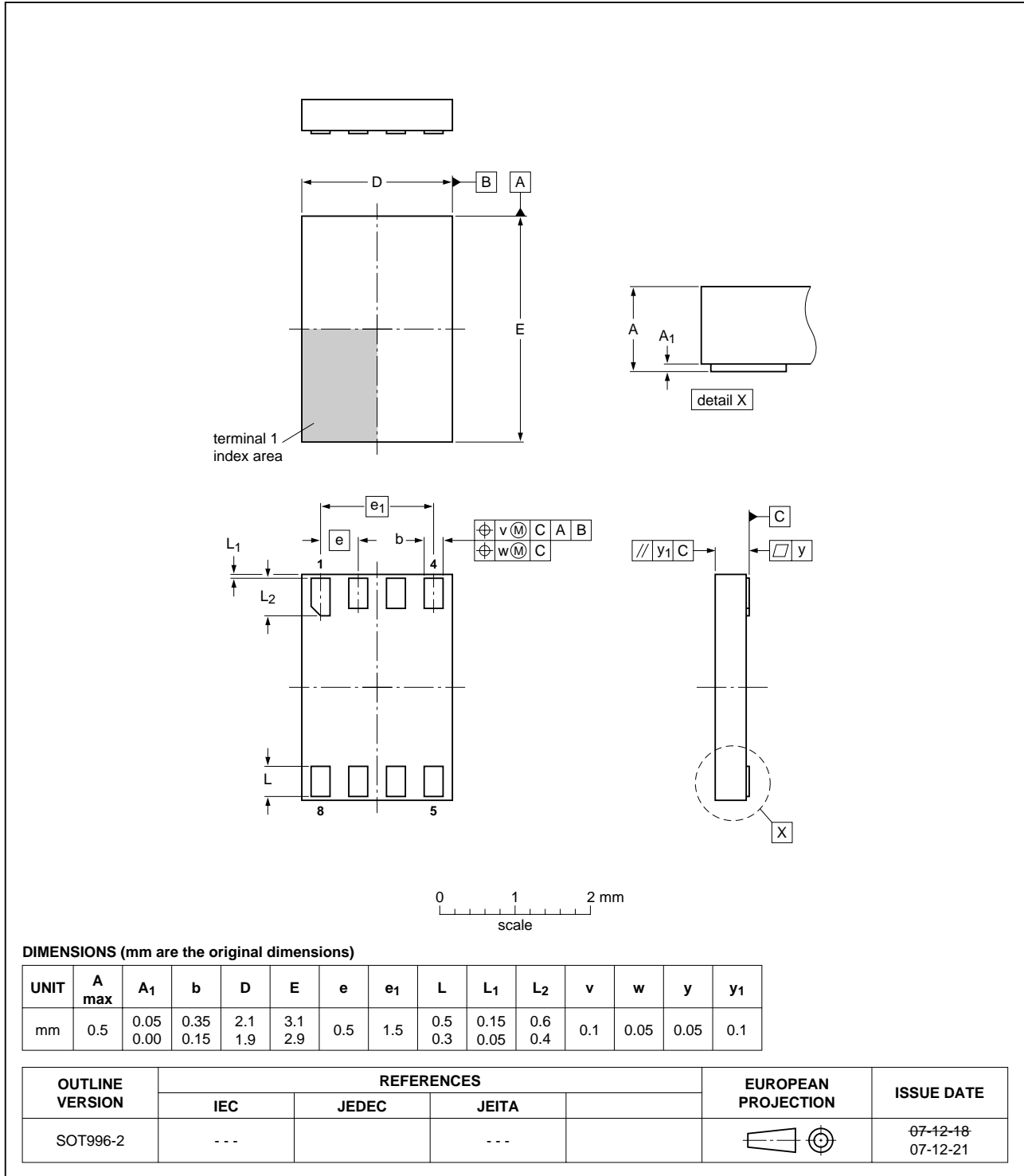


Fig 13. Package outline SOT996-2 (XSON8U)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1



Fig 14. Package outline SOT902-1 (XQFN8U)

## 14. Abbreviations

**Table 12. Abbreviations**

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 15. Revision history

**Table 13. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G74_4	20080603	Product data sheet	-	74AUP1G74_3
Modifications:	<ul style="list-style-type: none"> <li>Added type number 74AUP1G74GD (XSON8U package)</li> </ul>			
74AUP1G74_3	20080207	Product data sheet	-	74AUP1G74_2
74AUP1G74_2	20070515	Product data sheet	-	74AUP1G74_1
74AUP1G74_1	20060825	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 16.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

18. Contents

1 General description . . . . . 1

2 Features . . . . . 1

3 Ordering information . . . . . 2

4 Marking . . . . . 2

5 Functional diagram . . . . . 2

6 Pinning information . . . . . 3

6.1 Pinning . . . . . 3

6.2 Pin description . . . . . 4

7 Functional description . . . . . 4

8 Limiting values . . . . . 5

9 Recommended operating conditions . . . . . 5

10 Static characteristics . . . . . 6

11 Dynamic characteristics . . . . . 9

12 Waveforms . . . . . 15

13 Package outline . . . . . 18

14 Abbreviations . . . . . 22

15 Revision history . . . . . 22

16 Legal information . . . . . 23

16.1 Data sheet status . . . . . 23

16.2 Definitions . . . . . 23

16.3 Disclaimers . . . . . 23

16.4 Trademarks . . . . . 23

17 Contact information . . . . . 23

18 Contents . . . . . 24

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2008.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 3 June 2008

Document identifier: 74AUP1G74\_4





## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331